

PJD100P04E-AU

40V P-Channel Enhancement Mode MOSFET

Voltage -40 V **Current** -135 A

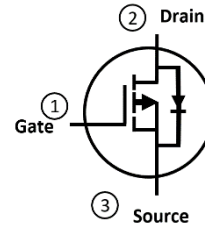
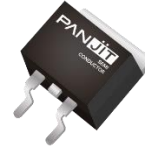
Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-20A < 5.2m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-10A < 7.3m\Omega$
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.3217 grams

TO-252AA



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 25	
Continuous Drain Current ^(Note 3)	$T_C=25^\circ\text{C}$	I_D	-135	A
	$T_C=100^\circ\text{C}$		-97	
Pulsed Drain Current ^(Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	-400	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	176	W
	$T_C=100^\circ\text{C}$		88	
Continuous Drain Current ^(Note 4)	$T_A=25^\circ\text{C}$	I_D	-18	A
	$T_A=70^\circ\text{C}$		-15	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	3	W
	$T_A=70^\circ\text{C}$		2.1	
Single Pulse Avalanche Current ^(Note 5)		I_{AS}	-22	A
Single Pulse Avalanche Energy ^(Note 5)		E_{AS}	186	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	$^\circ\text{C}$
Thermal Resistance ^(Note 4)	Junction to Case	$R_{\theta JC}$	0.85	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	50	

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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.8	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A	-	4.2	5.2	mΩ
		V _{GS} =-4.5V, I _D =-10A	-	5.6	7.3	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Q _g	V _{DS} =-32V, I _D =-20A, V _{GS} =-10V	-	142	190	nC
Gate-Source Charge	Q _{gs}		-	24	-	
Gate-Drain Charge	Q _{gd}		-	37	-	
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V, f=1MHz	-	7169	9400	pF
Output Capacitance	C _{oss}		-	695	980	
Reverse Transfer Capacitance	C _{rss}		-	541	760	
Gate resistance	R _g	f=1MHz	-	3.2	-	Ω
Turn-On Delay Time	td _(on)	V _{DS} =-32V, I _D =-20A, V _{GS} =-10V, R _G =3Ω (Note 2)	-	15	-	ns
Turn-On Rise Time	tr		-	31	-	
Turn-Off Delay Time	td _(off)		-	132	-	
Turn-Off Fall Time	tf		-	83	-	
Drain-Source Diode						
Diode Forward Current	I _s	T _C =25° C	-	-	-135	A
Pulsed Diode Forward Current	I _{SM}		-	-	-400	
Diode Forward Voltage	V _{SD}	I _S =-20A, V _{GS} =0V	-	-	-1.3	V
Reverse Recovery Time	T _{rr}	V _{DD} =-32V,V _{GS} =0V	-	24	-	ns
Reverse Recovery Charge	Q _{rr}	I _S =-20A,dI _S /dt=100A/us	-	15	-	nC

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\theta JC}=0.85^{\circ}\text{C/W}$, Package limited 100A.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
5. E_{AS} is calculated based on the condition of $L=1mH$, $I_{AS}=-19.3A$, $V_{DD}=-30V$, $V_{GS}=-10V$. 100% test at $L=0.5mH$, $I_{AS}=-22A$ in production.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

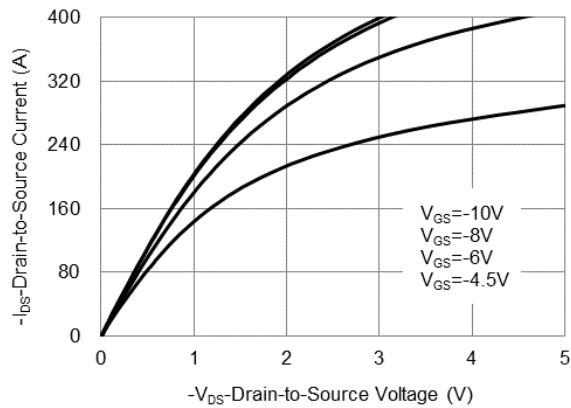


Fig.1 On-Region Characteristics

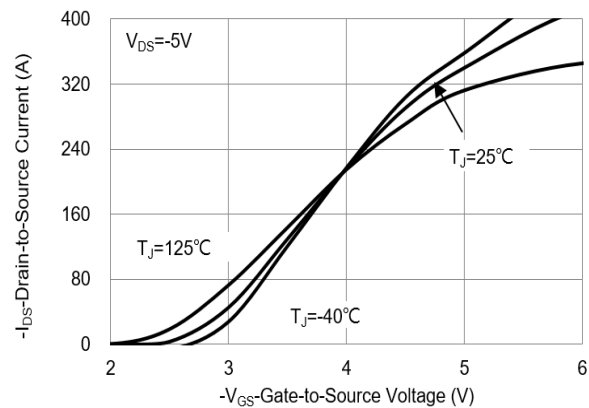


Fig.2 Transfer Characteristics

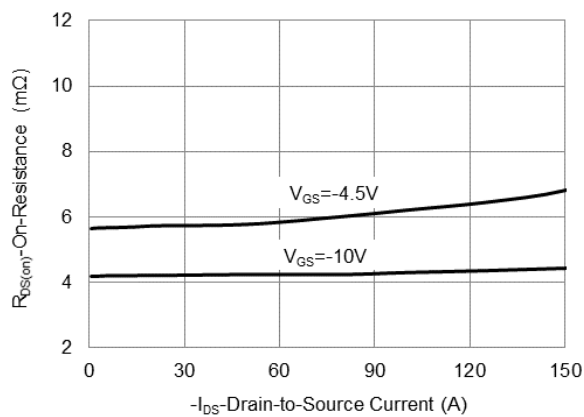


Fig.3 On-Resistance vs. Drain Current

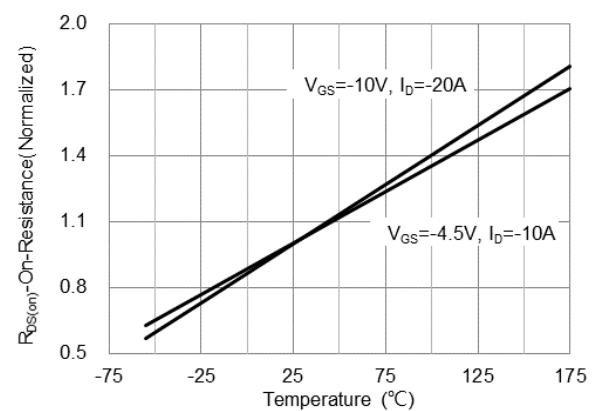


Fig.4 On-Resistance vs. Junction temperature

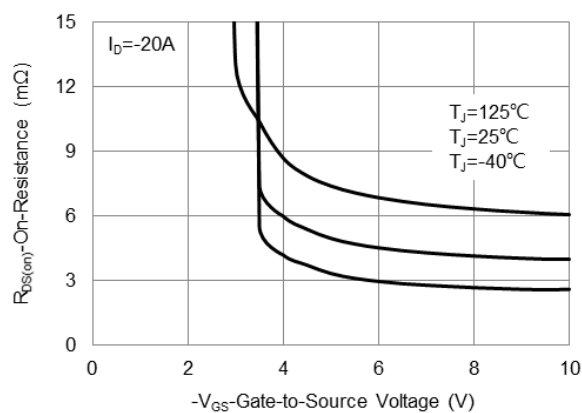


Fig.5 On-Resistance Variation with V_{GS}

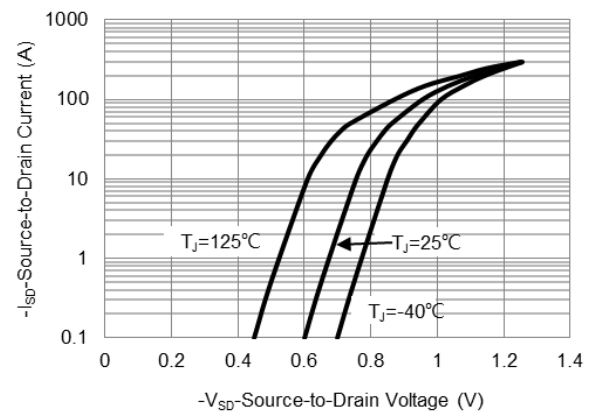
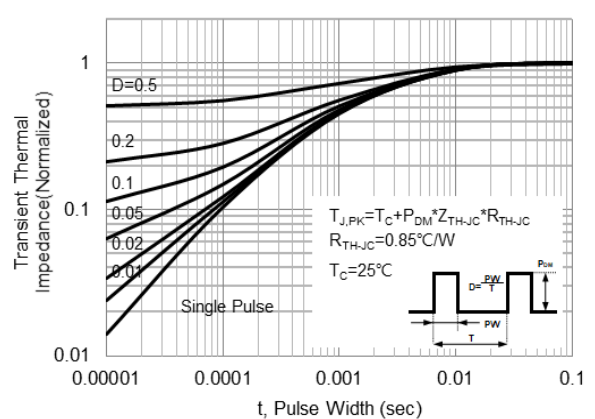
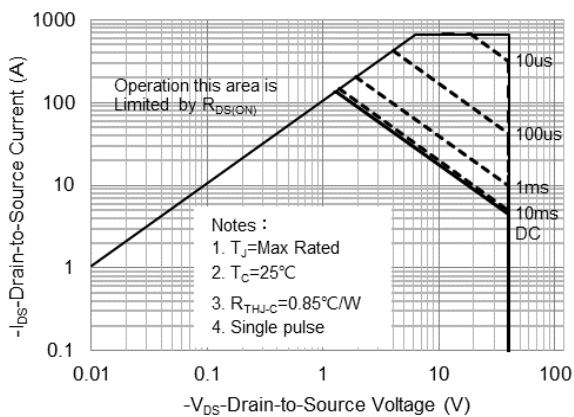
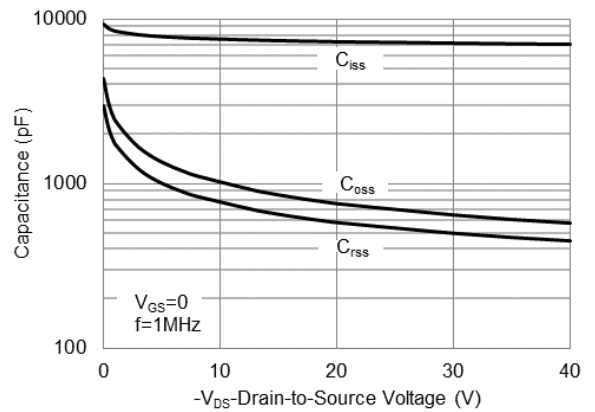
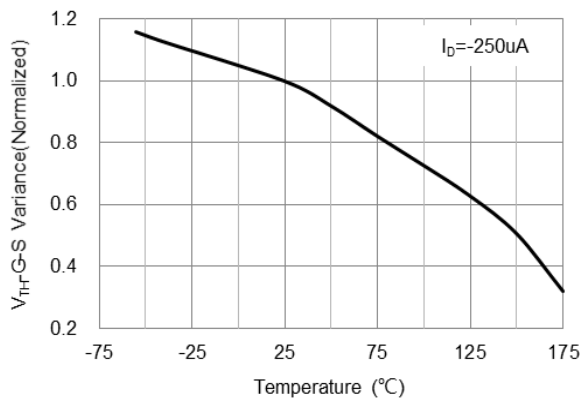
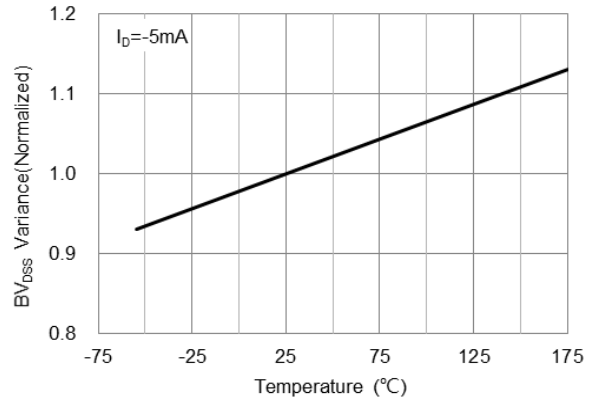
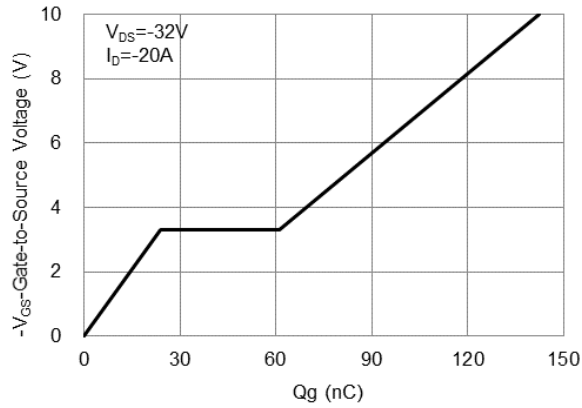


Fig.6 Source-Drain Diode Forward Voltage

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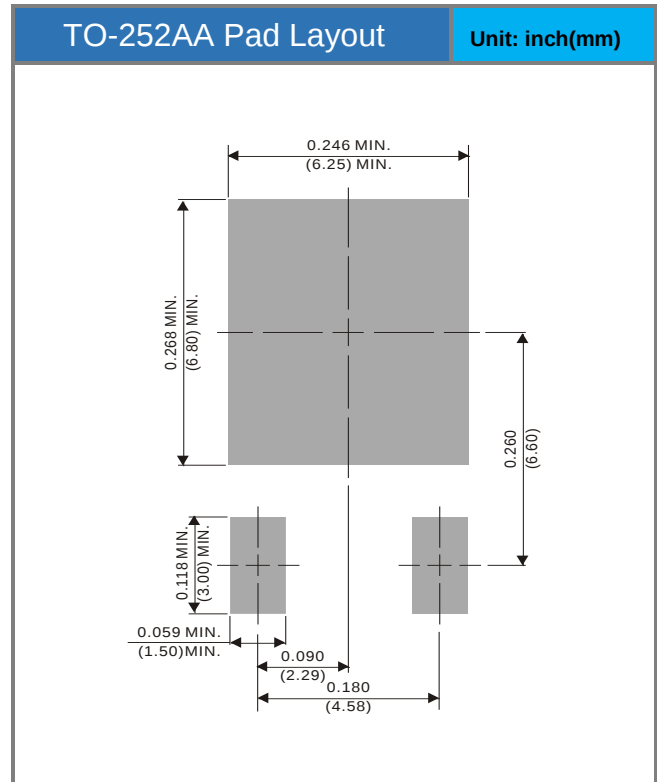
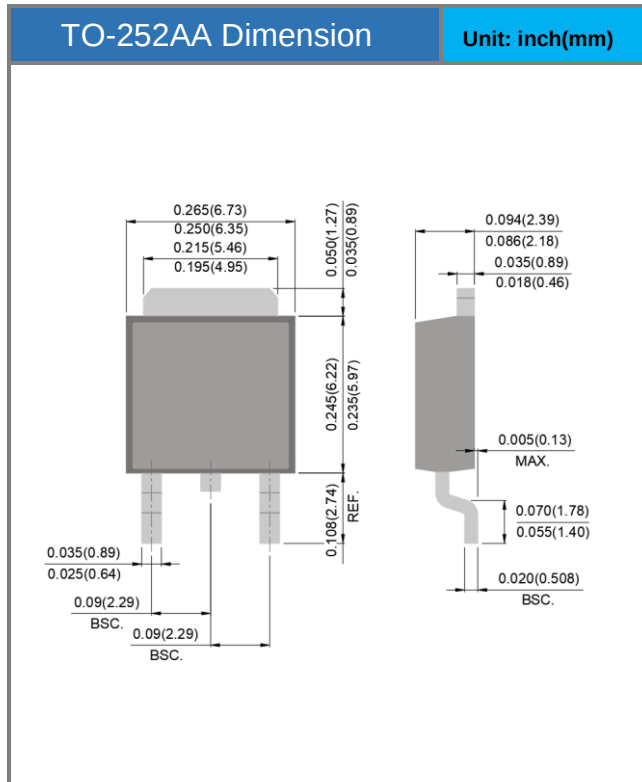


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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJD100P04E-AU	TO-252AA	3K pcs / 13" reel	100P04E

Packaging Information & Mounting Pad Layout



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